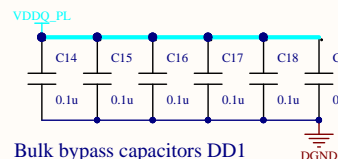
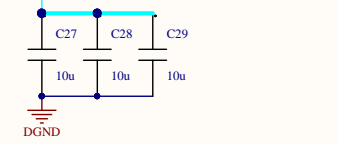


High-Speed bypass capacitors DD1



Bulk bypass capacitors DD1



CKE and RESET# require 4.75K resistor for PD, to maintain logic low through FPGA Configuration. See UG586p120

Layout Note:
DDR3L target trace impedances are:
Single Ended Signals = 40 ohms
Differential Signals = 80 ohms

Layout Note:
Use Fly-by routing and termination for DDR3L control signals.
Resistors should be placed past the last device as close to the device as possible.

Device Configuration Power for DDR3L

Revision :D/E/J

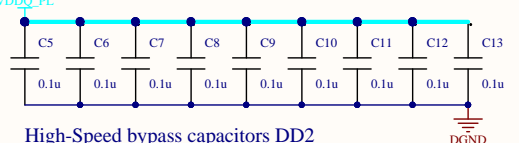
MT41J256M16RE-15E

DDR3 512MB 32M x 16 x 8 banks

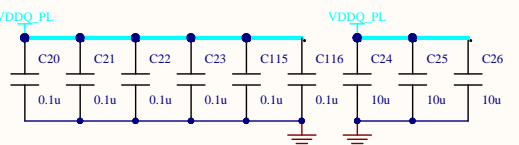
- VDD = VDDQ = 1.35V ± 0.075V
- 1.5ns @ CL = 9 (DDR3-1333) -15E
- TC of -40°C to 95°C; 64ms, 8192 cycle refresh at 0°C to 85°C; 32ms, 8192 cycle refresh at 85°C to 95°C

Rev D	Rev E/J		
Burst read operating current	240mA	Burst read operating current	202mA
Burst write operating current	200mA	Burst write operating current	152mA
Burst refresh current	210mA	Burst refresh current	228mA
All banks interleaved read current	285mA	All banks interleaved read current	217mA

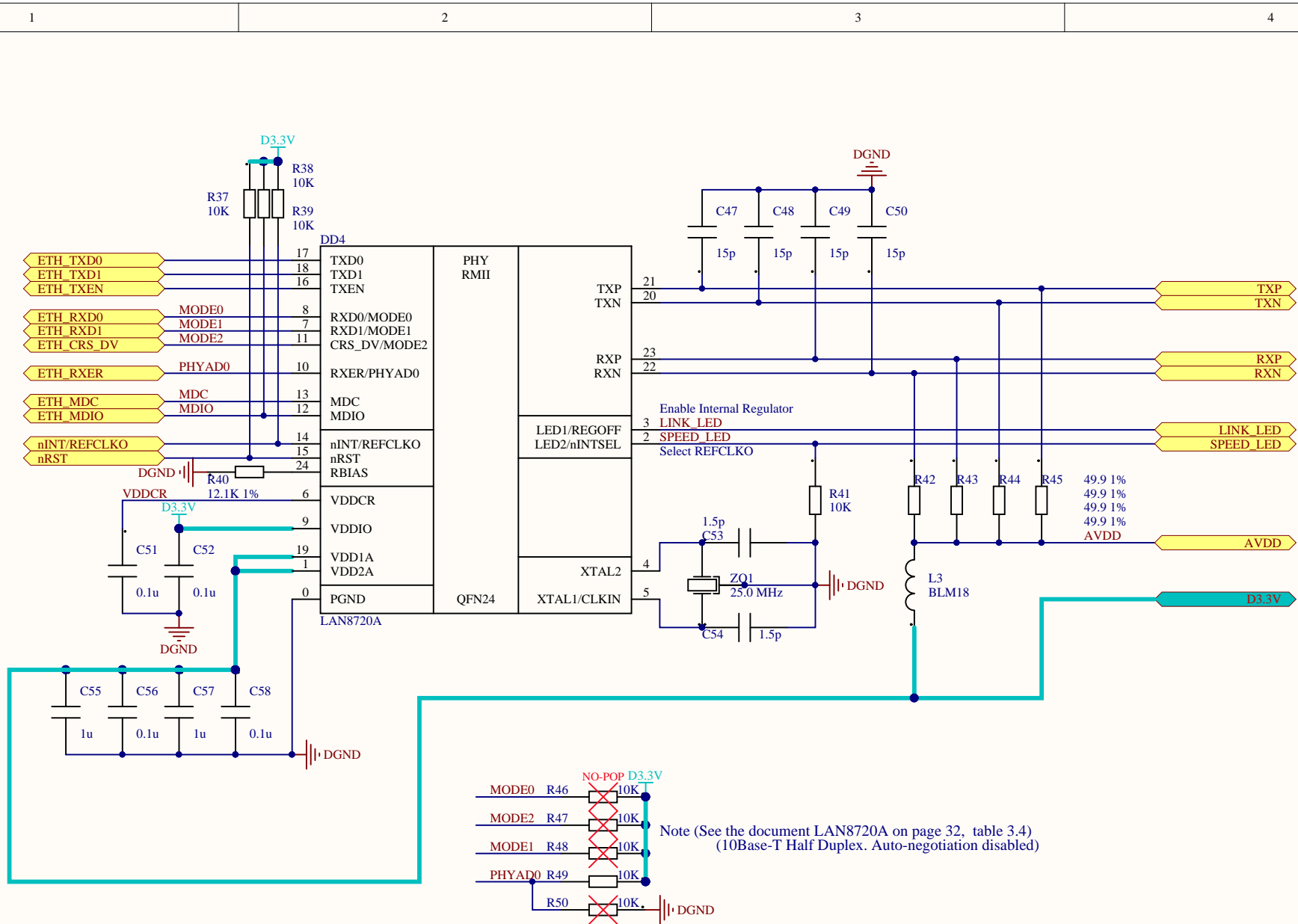
High-Speed bypass capacitors DD2



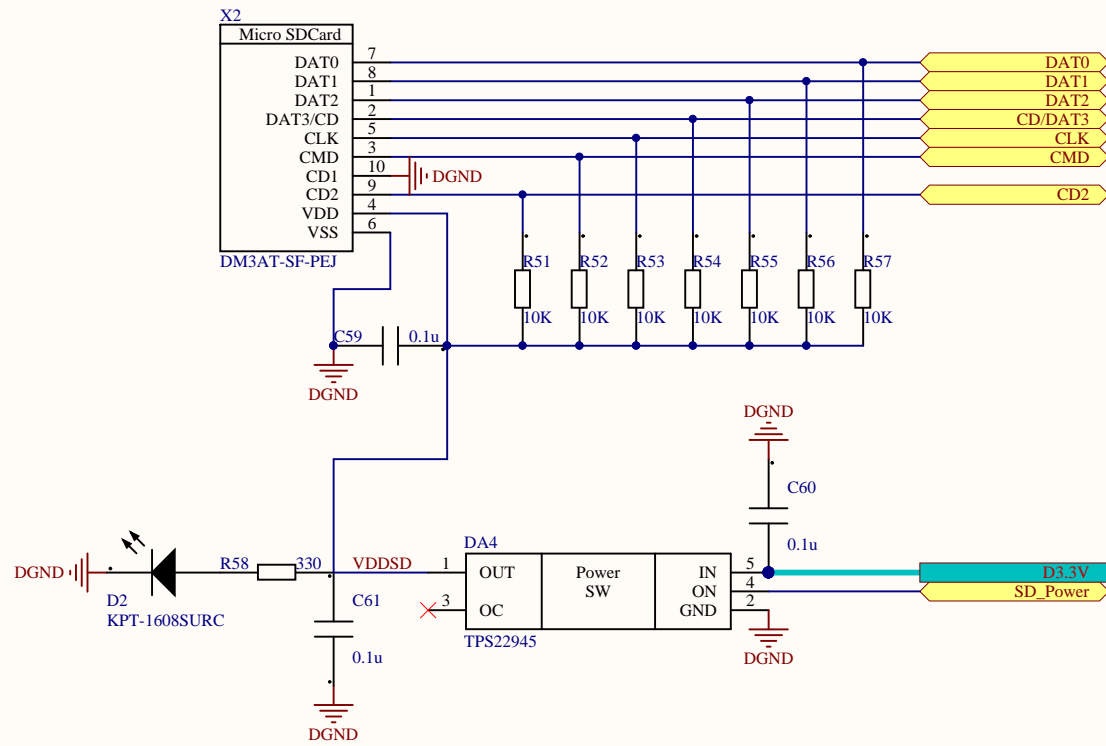
High-Speed bypass capacitors DD2



Bulk bypass capacitors DD2

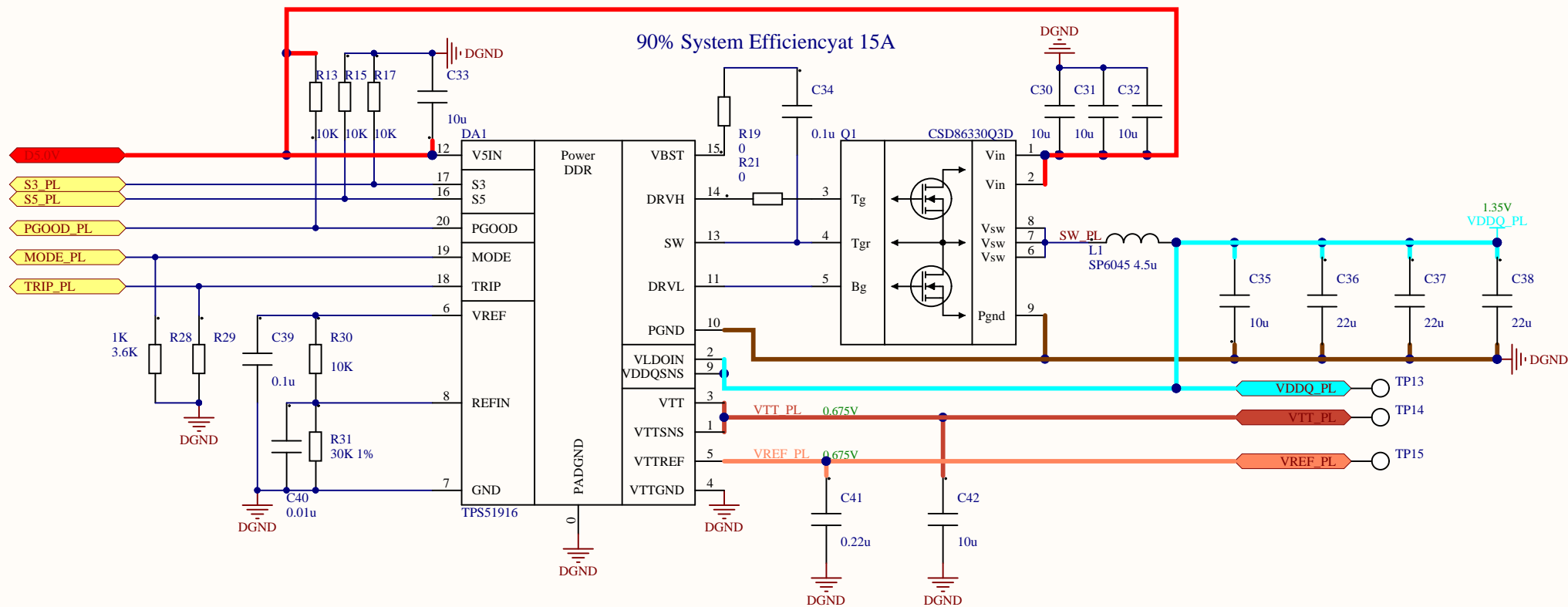


XC7A35T_PL_Ethernet



XC7A35T_PL_SDCard

90% System Efficiency at 15A



Device Configuration for DDR3/3L

▲ MODE: R = 1K Fsw = 500KHz
 TRIP: CDS86350Q5D Rds = 2mO Iocl = 2.5A Rtrip = 3.6K

 Vin = 5.5V VDDQ = 1.35V VTT = 0.675V
 Iout = 1.8A Iind(ripple) = 0.6A Iind(peak) = 2.75A Ivtt = 1.2A
 Cout > 57u

TPS51916_PW_DDR3L_PL

1

2

3

4

A

A

B

B

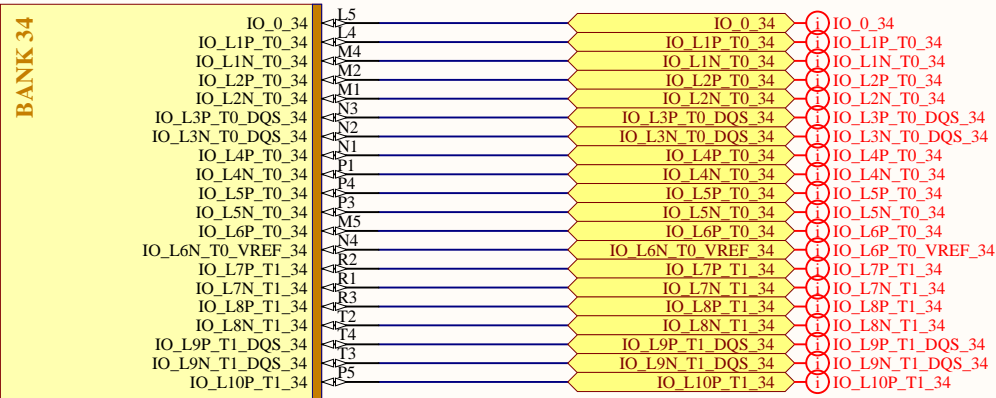
C

C

D

D

DD1D



XC7A35T-3FTG256E

DD1I



XC7A35T-3FTG256E

BANK34

1

2

3

4

1

2

3

4

A

A

B

B

C

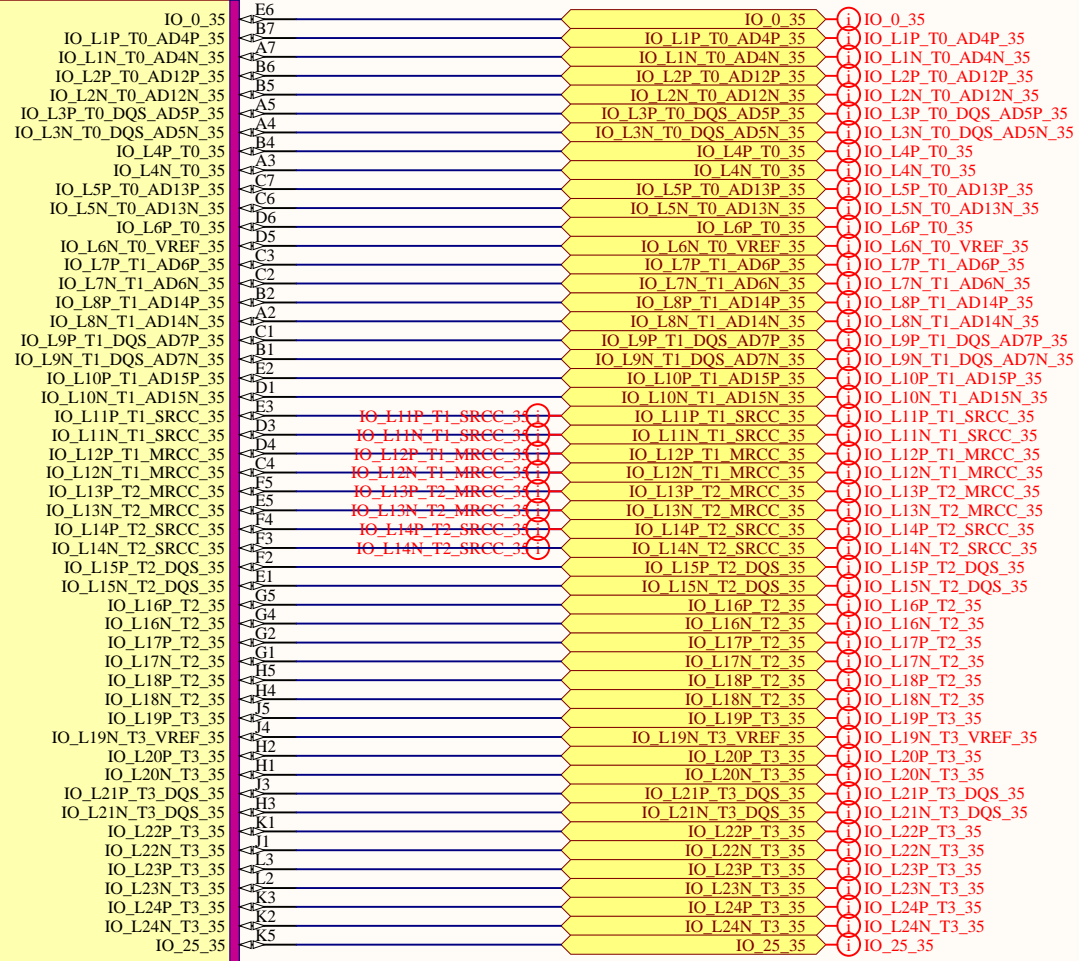
C

D

D

DDIE

BANK 35



XC7A35T-3FTG256E

DDIJ



XC7A35T-3FTG256E

BANK35

1

2

3

4